

L Number	Hits	Search Text	DB	Time stamp
1	68	(coat coating deposit depositing deposition film layer layering) near3 (silicon near (carbide nitride oxide dioxide) "si.sub.3.N.sub.4" "si.sub.3 n.sub.4" "sio.sub.2" "si O.sub.2" "SiC" "Si C") and ((438/121,122,for.436).CCLS.) and pd>=20031124	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 17:57
-	2	("20020121698").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 13:45
-	2	("6369452").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 15:30
-	2	("4939316").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 15:34
-	2	("5066368").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 15:34
-	1664	deposit\$3 near4 (insultaing insulator silicon near (oxide dioxide nitrid carbide)) with (heat nea (slug sink plate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 16:35
-	656	deposit\$3 near4 (insultaing insulator silicon near (oxide dioxide nitrid carbide)) near4 (heat nea (slug sink plate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 17:03
-	0	deposit\$3 near4 (insultaing insulator silicon near (oxide dioxide nitrid carbide)) near4 (heat near (slug sink plate)) not (deposit\$3 near4 (insultaing insulator silicon near (oxide dioxide nitrid carbide)) near4 (heat nea (slug sink plate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 17:03
-	0	deposit\$3 near4 (insultaing insulator silicon near (oxide dioxide nitrid carbide)) near4 ((metal metallic) near (slug sink plate)) not (deposit\$3 near4 (insultaing insulator silicon near (oxide dioxide nitrid carbide)) near4 (heat nea (slug sink plate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/11 17:04